Synthesis of Zn(Cu_xCd_yMg_z)Sforenhancingphosphorproperties

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Abstract: Because ZnS is a kind of wide band gap II–VI compound semiconductor materials ($E_g \sim 3.6 \text{ eV}$), ZnS become good host material for its energy band characteristic. In order to obtain photoluminescent emission (PL) spectrum of phosphor for red-shift color change, various metal ions as impurity are doped in ZnS nanocrystalline. Pure ZnS phosphor without other doped impurities emit blue light ($\lambda_{em} \sim 440 \text{ nm}$). After metal impurity was doped to ZnS, new luminescent centers could be formed that emission of phosphor would be red-shift. Main emission of phosphor could be observed at green light ($\lambda_{em} \sim 505 \text{ nm}$) of ZnS:Cu. Against to such a fact, enhance mechanisms for luminescence intensity and lifetime of luminescence are still insufficient for theirs' wide applications. In this paper, while Cu doped ZnS was preparing by co-precipitation process, following Cd and Mg addition. At last, Zn(Cu_xCd_yMg_z)S as a new phosphor could be obtained. Structure and composition of Zn(Cu_xCd_yMg_z)S phosphor were investigated by luminescence spectrometer. As a result of comparing with other Cu doped ZnS phosphor, Zn(Cu_xCd_yMg_z)S could be confirmed having much stronger luminescence intensity and longer luminescence lifetime.

Keywords: doped ZnS; Luminescence; Copper; Cadmium; Energy transfer, Zn(CuxCdyMgz)Sphosphor